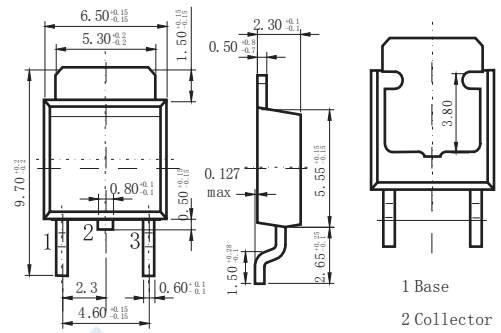
PNP Transistors

2SB967

TO-252

Unit: mm



1 Base
2 Collector
3 Emitter

■ Features

- Large collector current Ic
- Low collector to emitter saturation voltage $V_{CE(sat)}$.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-27	V
Collector - Emitter Voltage	V_{CEO}	-18	
Emitter - Base Voltage	V_{EBO}	-7	
Collector Current - Continuous	I_C	-5	A
Collector current -Pulse	I_{CP}	-8	
Collector Power Dissipation	P_C	20	W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-27			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA, I_B=0	-18			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C=0	-7			
Collector-base cut-off current	I_{CBO}	V_{CB}= -20V , I_E=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-3 A, I_B=-100mA			-1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-3 A, I_B=-100mA			-1.2	
DC current gain	h_{FE}	V_{CE}= -2V, I_C= -2 A	90		625	
Collector output capacitance	C_{ob}	V_{CB} = –20V, I_E = 0, f = 1MHz			85	pF
Transition frequency	f_T	V_{CE}= -6V, I_E= 50mA,f=200MHz		120		MHz

■ Classification of h_{fe}

Type	2SB967-P	2SB967-Q	2SB967-R
Range	90-135	125-205	180-625

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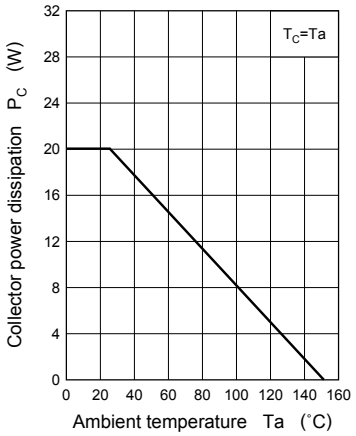
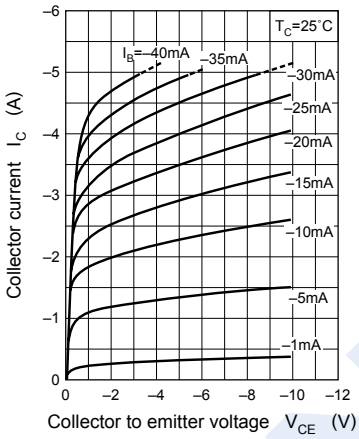
■ Typical Characterisitics

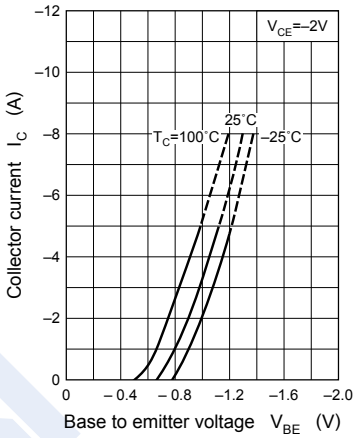
P_C — Ta



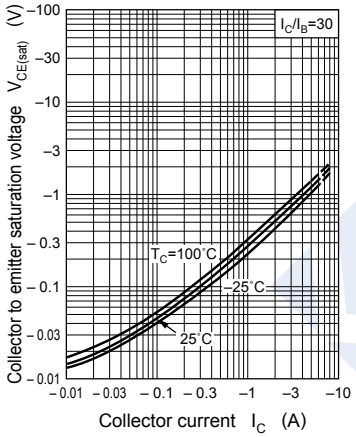
I_C — V_{CE}



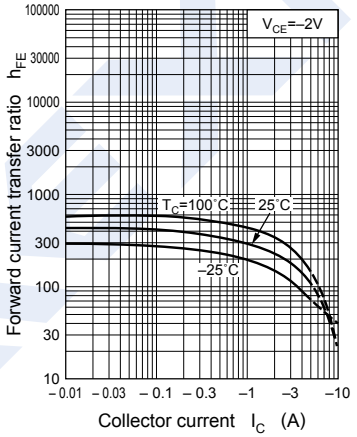
I_C — V_{BE}



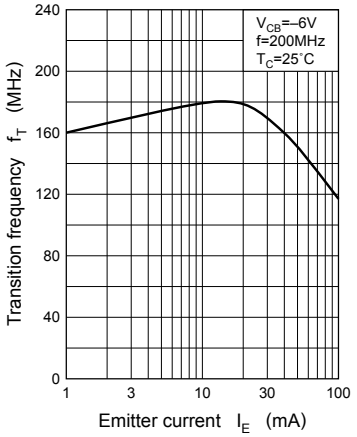
$V_{CE(sat)}$ — I_C



h_{FE} — I_C



f_T — I_E



C_{ob} — V_{CB}